

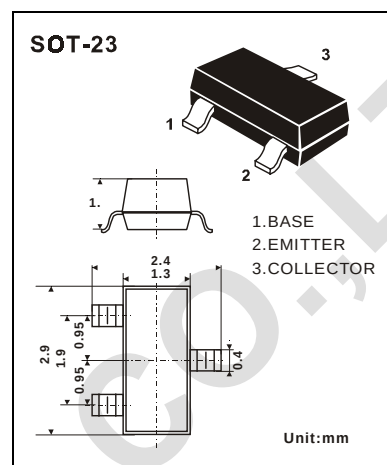
NPN EPITAXIAL SILICON TRANSISTOR

* Complement to 2SA1015

* Collector Current :I_c=150mA

ABSOLUTE MAXIMUM RATINGS at Ta=25°C

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{cb0}	60	V
Collector-Emitter Voltage	V _{ceo}	50	V
Emitter-Base Voltage	V _{eb0}	5	V
Collector Current	I _c		mA
Collector Dissipation Ta=25°C*	P _D	225	mW
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55-150	°C



ELECTRICAL CHARACTERISTICS at Ta=25°C

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BV _{cb0}	60			V	I _c =100uA I _e =0
Collector-Emitter Breakdown Voltage#	BV _{ceo}	50			V	I _c = 1mA I _b =0
Emitter-Base Breakdown Voltage	BV _{eb0}	5.0			V	I _e = 100uA I _c =0
Collector-Base Cutoff Current	I _{cbo}			100	nA	V _{cb} = 50V I _e =0
Emitter-Base Cutoff Current	I _{ebo}			100	nA	V _{eb} = 3V I _c = 0
DC Current Gain	H _{fe}	70		700		V _{ce} = 6V I _c = 2mA
Collector-Emitter Saturation Voltage	V _{ce(sat)}			0.30	V	I _c = 100mA I _b = 10mA

* Total Device Dissipation : FR=1x0.75x0.062in Board,Derate 25°C.

Pulse Test : Pulse Width ≤300uS,Duty cycle ≤2%

DEVICE MARKING:

2SC1815=L6